



NCE N-Channel Super Trench Power MOSFET

Description

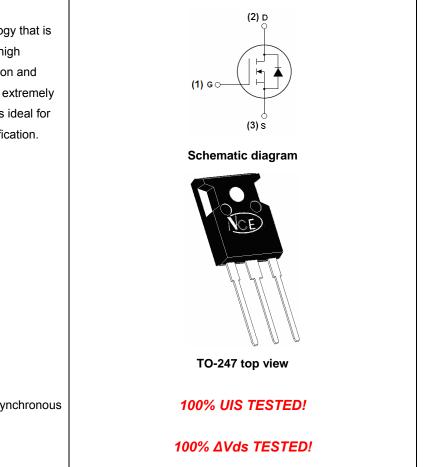
The NCEP01T18T uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

General Features

- V_{DS} =100V,I_D =180A
 R_{DS(ON)} <3.0mΩ @ V_{GS}=10V
- Excellent gate charge x R_{DS(on)} product(FOM)
- Very low on-resistance R_{DS(on)}
- 175 °C operating temperature
- Pb-free lead plating
- 100% UIS tested

Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP01T18T	NCEP01T18T	TO-247	-	-	-

Absolute Maximum Ratings (T_c=25℃ unless otherwise noted)

Parameter	Symbol	Limit	Unit		
Drain-Source Voltage	Vds	100	V		
Gate-Source Voltage	Vgs	±20	V		
Drain Current-Continuous	I _D	180	А		
Drain Current-Continuous(T _C =100℃)	I _D (100℃)	128	A		
Pulsed Drain Current	I _{DM}	720	A		
Maximum Power Dissipation	PD	300	W		
Derating factor		2	W/℃		
Single pulse avalanche energy (Note 5)	E _{AS}	1800	mJ		
Operating Junction and Storage Temperature Range	T_{J},T_{STG}	-55 To 175	°C		
Thermal Characteristic					
Thermal Resistance, Junction-to-Case ^(Note 2)	R _{θJC}	0.5	°C /W		





Electrical Characteristics (Tc=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics	· ·		·			
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA	100		-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =100V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V_{GS} =±20V, V_{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)	· ·		·			
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS}$, I _D =250µA	2.5	-	4.5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V_{GS} =10V, I _D =100A	-		3.0	mΩ
Forward Transconductance	g fs	V _{DS} =10V,I _D =50A	40	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{lss}		-	11500	-	PF
Output Capacitance	C _{oss}	V _{DS} =50V,V _{GS} =0V, F=1.0MHz	-	2480	-	PF
Reverse Transfer Capacitance	Crss	F=1.0MHZ	-	75	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}		-	25	-	nS
Turn-on Rise Time	tr	V _{DD} =50V,I _D =100A	-	75	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10V, R_{G} =1.6 Ω	-	89	-	nS
Turn-Off Fall Time	t _f		-	29	-	nS
Total Gate Charge	Qg		-	158		nC
Gate-Source Charge	Q _{gs}	V_{DS} =50V,I _D =100A,	-	52		nC
Gate-Drain Charge	Q _{gd}	V _{GS} =10V	-	29		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =180A	-		1.2	V
Diode Forward Current (Note 2)	Is		-	-	180	А
Reverse Recovery Time	t _{rr}	T_J = 25°C, I_F = I_S	-	75		nS
Reverse Recovery Charge	Qrr	di/dt = 100A/µs ^(Note3)	-	185		nC

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.

2. Surface Mounted on FR4 Board, t ≤ 10 sec.

3. Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.

4. Guaranteed by design, not subject to production

5. EAS condition : Tj=25 $^\circ \!\! C$,V_DD=50V,V_G=10V,L=0.5mH,Rg=25\Omega

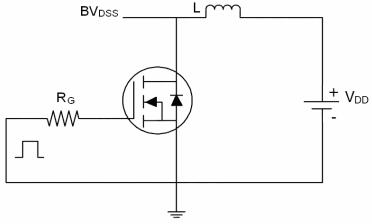


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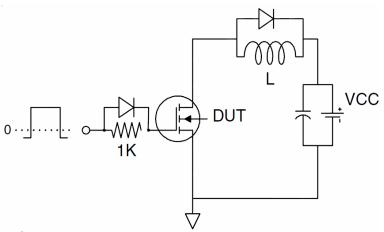




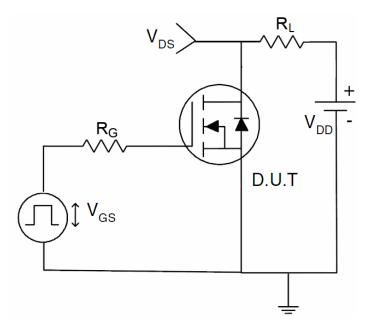
Test Circuit 1) E_{AS} test Circuit



2) Gate charge test Circuit



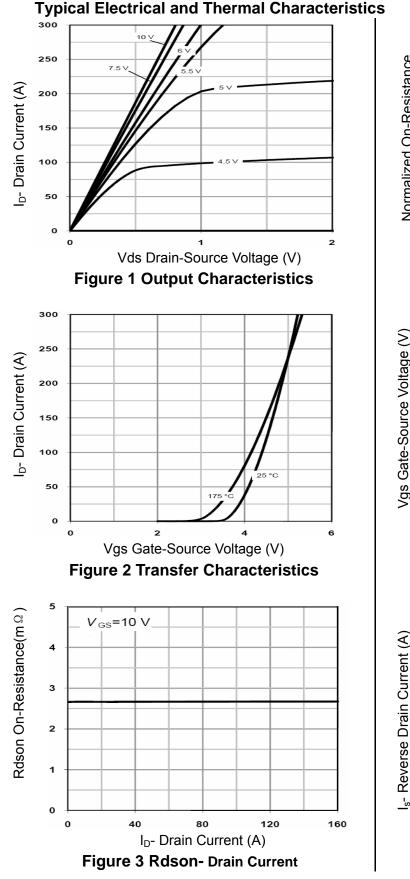
3) Switch Time Test Circuit

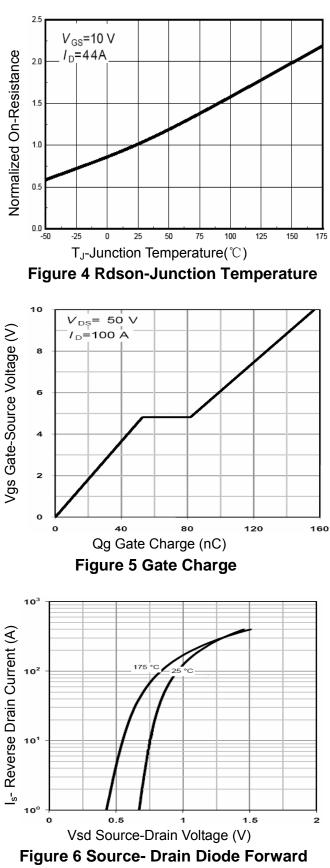




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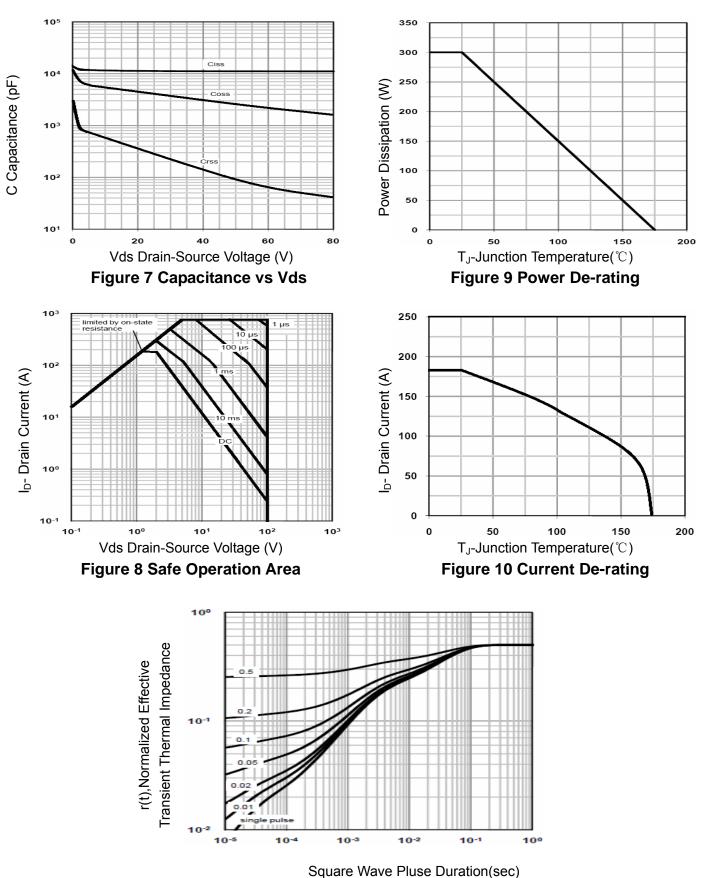


Figure 11 Normalized Maximum Transient Thermal Impedance

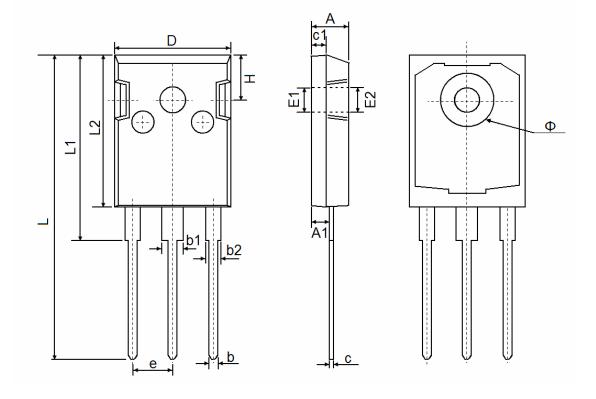


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TO-247 Package Information



Symbol	Dimensions	In Millimeters	Dimensions In Inches		
	Min.	Max.	Min.	Max.	
A	4.850	5.150	0.191	0.200	
A1	2.200	2.600	0.087	0.102	
b	1.000	1.400	0.039	0.055	
b1	2.800	3.200	0.110	0.126	
b2	1.800	2.200	0.071	0.087	
С	0.500	0.700	0.020	0.028	
c1	1.900	2.100	0.075	0.083	
D	15.450	15.750	0.608	0.620	
E1	3.500 REF		0.138 REF		
E2	3.600 REF		0.142 REF		
L	40.900	41.300	1.610	1.626	
L1	24.800	25.100	0.976	0.988	
L2	20.300	20.600	0.799	0.811	
Ф	7.100	7.300	0.280	0.287	
e	5.450 TYP		0.215 TYP		
Н	5.980 REF		0.235 REF		







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